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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet	1	of	8

Complete if Known	
Application Number	09/938,672
Filing Date	August 27, 2001
First Named Inventor	John T. Moore
Art Unit	2152
Examiner Name	T. Washington
Attorney Docket Number	M4065.0475/P475

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
MDP	AA	6,388,324	05/14/2002	Kozicki et al.	
	AB	US 2002/0000666	01/03/2002	Kozicki et al.	
	AC	5,500,532	03/19/1996	Kozicki et al.	
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	AE	5,751,012	05/12/1998	Wolstenholme et al.	
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MDP	AG	6,348,365	02/19/2202	Moore et al.	

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Examiner Initials*	Cite No.[1]	Foreign Patent Document Country Code[3]-Number[4]-Kind Code[5] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
MDP	BA	WO 02/21542	03/14/2002	Kozicki et al.		
MDP	BB	WO 00/48196	08/17/2000	Kozicki et al.		
MDP	BC	WO 97/48032	12/18/1997	Kozicki et al.		
MDP	BD	WO 99/28914	06/10/1999	Kozicki et al.		

Examiner Signature		Date Considered	

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Sheet 2 of 8

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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Sheet 4 of 8

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Group Art Unit	2152
Examiner Name	T. Washington
Attorney Docket Number	M4065.0475/P475

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Sheet 7 of 8

Complete if Known	
Application Number	09/938,672
Filing Date	August 27, 2001
First Named Inventor	John T. Moore
Group Art Unit	2152
Examiner Name	T. Washington
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Sheet 8 of 8

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Filing Date	August 27, 2001
First Named Inventor	John T. Moore
Group Art Unit	2152
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Attorney Docket Number	M4065.0475/P475

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Sheet 1 of 1

Complete if Known	
Application Number	09/938,672
Filing Date	August 27, 2001
First Named Inventor	John Moore
Art Unit	2152
Examiner Name	T. Washington
Attorney Docket Number	M4065.0475/P475

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Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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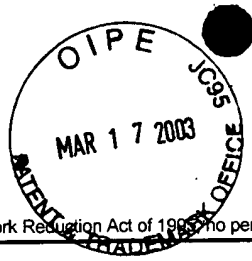

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Filing Date	February 13, 2003
First Named Inventor	John Moore
Art Unit	2151
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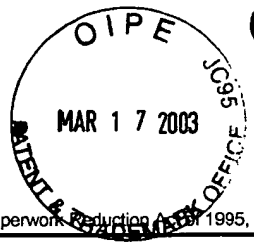

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First Named Inventor	John Moore
Art Unit	2151
Examiner Name	Not Yet Assigned
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MDP	AV1	2003/0027416 APP	2/6/2003	Moore	
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↓	CN	Owen et al., *Metal-Chalcogenide Photoresists for High Resolution Lithography and Sub-Micron Structures*, NANOSTRUCTURE PHYSICS AND FABRICATION, pp. 447-451 (M. Reed ed. 1989).	
HN	CO	Shimizu et al., *The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses*, 46 B. CHEM SOC. JAPAN, No. 12, pp. 3662-3365 (1973).	

Examiner Signature	[signature]	Date Considered	4/22/2003

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet	1	of	4

Complete if Known	
Application Number	09/938,672
Filing Date	August 27, 2001
First Named Inventor	John Moore
Art Unit	2151
Examiner Name	T. Washington
Attorney Docket Number	M4065.0475/P475

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Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Sheet 2 of 4

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Application Number	09/938,672
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First Named Inventor	John Moore
Art Unit	2151
Examiner Name	T. Washington
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Sheet 3 of 4

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Filing Date	August 27, 2001
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Examiner Name	T. Washington
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Examiner Initials*	Cite No.[1]	Foreign Patent Document: Country Code[3]-Number[4]-Kind Code[5] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
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	BB					

Examiner Signature	Marcel Tignac-Bruce	Date Considered	8/18/2003

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet	4	M4	4

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Application Number	09/938,672
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First Named Inventor	John Moore
Group Art Unit	2151
Examiner Name	T. Washington
Attorney Docket Number	M4065.0475/P475

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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	CN	Owen et al., *Metal-Chalcogenide Photoresists for High Resolution Lithography and Sub-Micron Structures*, NANOSTRUCTURE PHYSICS AND FABRICATION, pp. 447-451 (M. Reed ed. 1989).	
	CO	Shimizu et al., *The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses*, 46 B. CHEM SOC. JAPAN, No. 12, pp. 3662-3365 (1973).	
	CP		
	CQ		

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